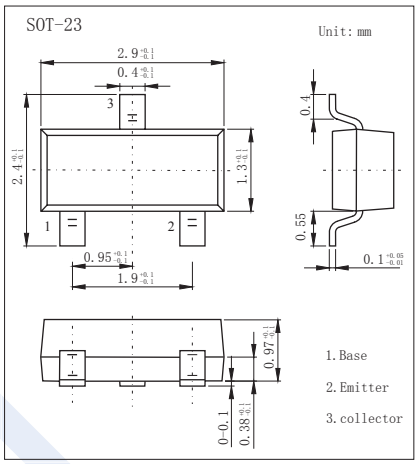
PNP Transistors

FMMT718 (KMMT718)



■ Features

- 625mW power dissipation.
- Ic CONT 2.5A.
- Ic up to 10A peak pulse current.
- Excellent hfe characteristics up to 10A (pulsed).
- Extremely low saturation voltage e.g. 10mV typ..
- Exhibits extremely low equivalent on-resistance; $R_{CE(sat)}$.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-20	V
Collector - Emitter Voltage	V_{CEO}	-20	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-1.5	A
Peak Collector Current	I_{CM}	-6	
Base Current	I_B	-500	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

PNP Transistors

FMMT718 (KMMT718)

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100uA	-20	-65		V
Collector-emitter breakdown voltage *	$V_{(BR)CEO}$	I_C=-10mA	-20	-55		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100uA	-5	-8.8		V
Collector cutoff current	I_{CBO}	V_{CB}=-15V			-100	nA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V			-100	nA
Collector-emitter saturation voltage *	$V_{CE(sat)}$	I_C=-0.1A, I_B=-10mA I_C=-1A, I_B=-10mA I_C=-1.5A, I_B=-50mA		-16 -130 -145	-40 -200 -220	mV
Base-emitter saturation voltage *	$V_{BE(sat)}$	I_C=-1.5A,I_B=-50mA		-0.87	-1	V
Base-emitter voltage *	$V_{BE(ON)}$	I_C=-2A,V_{CE}=-2V		-0.81	-1	V
DC current gain *	h_{FE}	I_C=-10mA, V_{CE}=-2V I_C=-0.1A, V_{CE}=-2V I_C=-2A, V_{CE}=-2V I_C=-4A, V_{CE}=-2V I_C=-6A, V_{CE}=-2V	300 300 150 35 15	475 450 230 70 30		
Current-gain-bandwidth product	f_T	I_C=-50mA,V_{CE}=-10V,f=100MHz	150	180		MHz
Output capacitance	C_{obo}	V_{CB}=-10V,f=1MHz		21	30	pF
Turn-on time	$t_{(on)}$	V_{CC}=-10V, I_C=-1A		40		ns
Turn-off time	$t_{(off)}$	I_{B1}=-I_{B2}=-20mA		670		ns

* Pulse test: tp ⩽ 300 ìs; d ⩽ 0.02.

■ Marking

Marking	718